

Silicon Standard Recovery Diode

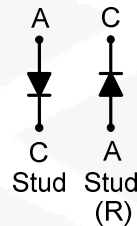
 $V_{RRM} = 800\text{ V} - 1000\text{ V}$
 $I_F = 12\text{ A}$

Features

- High Surge Capability
- Types from 800 V to 1000 V V_{RRM}
- Not ESD Sensitive

Note:

1. Standard polarity: Stud is cathode.
2. Reverse polarity (R): Stud is anode.
3. Stud is base.

DO-4 Package


Maximum ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	1N3671A (R)	1N3673A (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		800	1000	V
RMS reverse voltage	V_{RMS}		560	700	V
DC blocking voltage	V_{DC}		800	1000	V
Continuous forward current	I_F	$T_C \leq 150\text{ °C}$	12	12	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$, $t_p = 8.3\text{ ms}$	240	240	A
Operating temperature	T_j		-55 to 150	-55 to 150	°C
Storage temperature	T_{stg}		-55 to 150	-55 to 150	°C

Electrical characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	1N3671A (R)	1N3673A (R)	Unit
Diode forward voltage	V_F	$I_F = 12\text{ A}$, $T_j = 25\text{ °C}$	1.1	1.1	V
Reverse current	I_R	$V_R = 50\text{ V}$, $T_j = 25\text{ °C}$	10	10	μA
		$V_R = 50\text{ V}$, $T_j = 175\text{ °C}$	15	15	mA

Thermal characteristics

Parameter	Symbol	Conditions	1N3671A (R)	1N3673A (R)	Unit
Thermal resistance, junction - case	R_{thJC}		2.00	2.00	°C/W

Figure .1-Typical Forward Characteristics

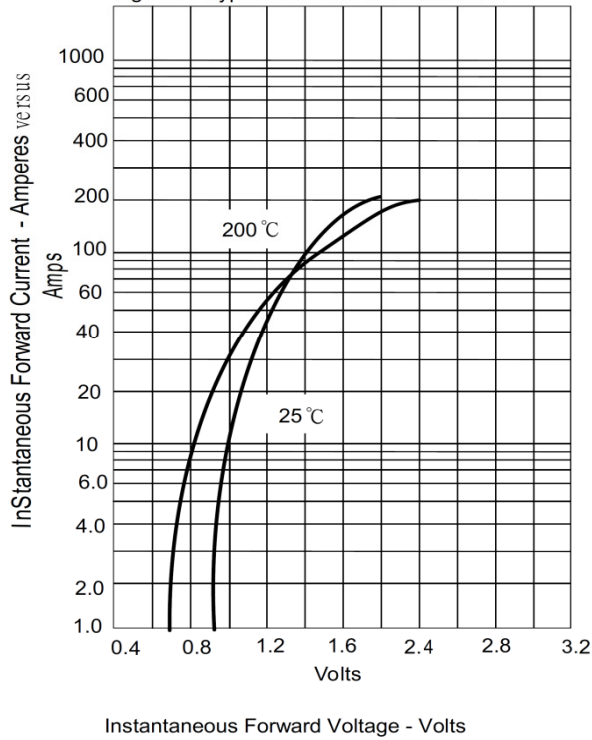


Figure .2- Forward Derating Curve

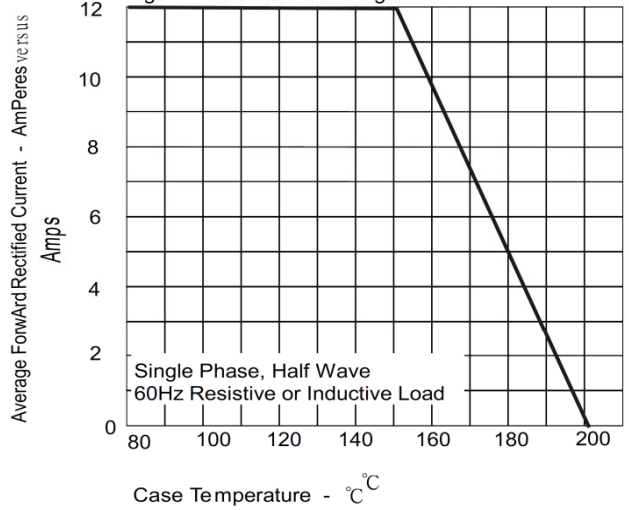


Figure .4-Typical Reverse Characteristics

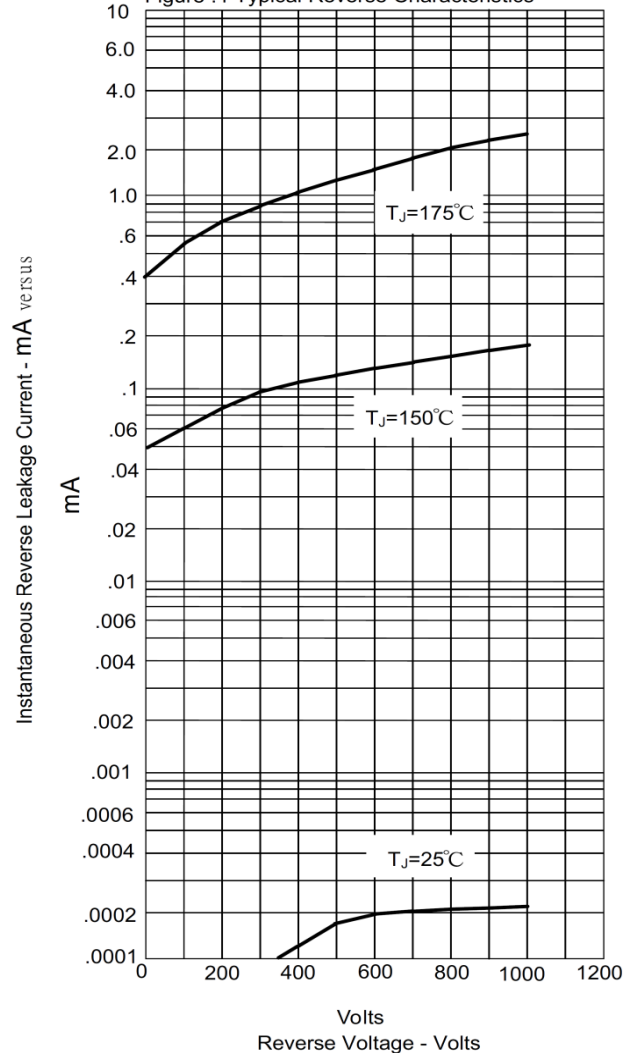
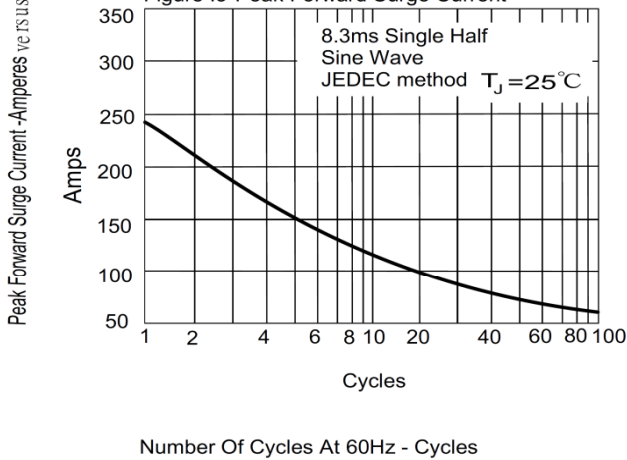
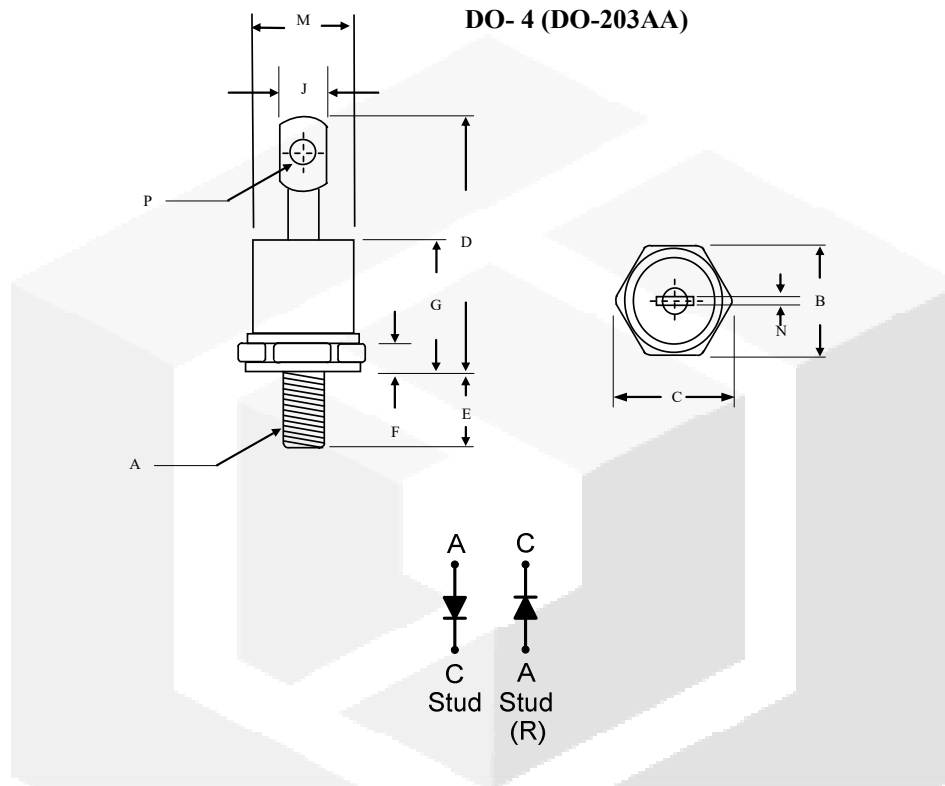


Figure .3-Peak Forward Surge Current



Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.



	Inches		Millimeters	
	Min	Max	Min	Max
A	10-32 UNF			
B	0.424	0.437	10.77	11.10
C	-----	0.505	-----	12.82
D	-----	0.800	-----	20.30
E	0.453	0.492	11.50	12.50
F	0.114	0.140	2.90	3.50
G	-----	0.405	-----	10.29
J	-----	0.216	-----	5.50
M	-----	φ0.302	-----	φ7.68
N	0.031	0.045	0.80	1.15
P	0.070	0.79	1.80	2.00